

2N3789 2N3791
2N3790 2N3792

**SILICON
PNP POWER TRANSISTORS**



TO-3 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3789, 2N3790, 2N3791, and 2N3792 are silicon PNP power transistors, manufactured by the epitaxial planar process, designed for medium speed switching and amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Continuous Base Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	2N3789	2N3790	UNITS
	2N3791	2N3792	
V_{CBO}	60	80	V
V_{CEO}	60	80	V
V_{EBO}		7.0	V
I_C		10	A
I_B		4.0	A
P_D		150	W
T_J, T_{stg}		-65 to +200	$^\circ\text{C}$
θ_{JC}		1.17	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3789		2N3790		UNITS
		2N3791	2N3792	2N3791	2N3792	
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}$	-	1.0	-	1.0	mA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{EB}=1.5\text{V}, T_C=150^\circ\text{C}$	-	5.0	-	5.0	mA
I_{EBO}	$V_{EB}=7.0\text{V}$	-	5.0	-	5.0	mA
BV_{CEO}	$I_C=200\text{mA}$	60	-	80	-	V
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=400\text{mA}$ (2N3789, 2N3790)	-	1.0	-	1.0	V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=500\text{mA}$ (2N3791, 2N3792)	-	1.0	-	1.0	V
$V_{BE(ON)}$	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$ (2N3789, 2N3790)	-	2.0	-	2.0	V
$V_{BE(ON)}$	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$ (2N3791, 2N3792)	-	1.8	-	1.8	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=10\text{A}$	-	4.0	-	4.0	V
h_{FE}	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$ (2N3789, 2N3790)	25	90	25	90	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=1.0\text{A}$ (2N3791, 2N3792)	50	180	50	180	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=3.0\text{A}$ (2N3789, 2N3790)	15	-	15	-	
h_{FE}	$V_{CE}=2.0\text{V}, I_C=3.0\text{A}$ (2N3791, 2N3792)	30	-	30	-	
f_T	$V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{MHz}$	4.0	-	4.0	-	MHz

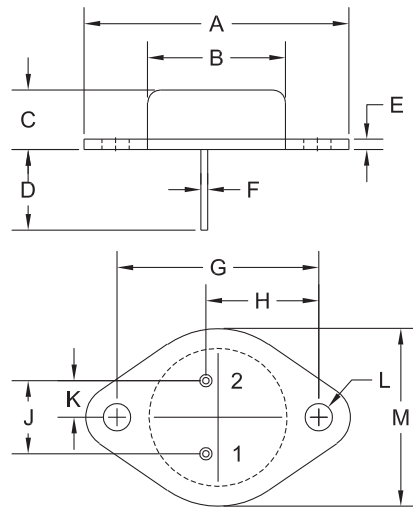
R2 (31-July 2013)

2N3789 2N3791
2N3790 2N3792

SILICON
PNP POWER TRANSISTORS



TO-3 CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

LEAD CODE:

- 1) Base
- 2) Emitter
- Case) Collector

MARKING:

FULL PART NUMBER

R2 (31-July 2013)